

# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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<b>Title of Invention</b>	<b>SEMICONDUCTOR DEVICE</b>
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Application Number :

Confirmation Number:

First Named Applicant: Kaoru INOUE

Attorney Docket Number: 28569.7636

Art Unit: 2814

Examiner: Long Pham

Search string: ( 6639255 or 6483135 or 6274889 or 6184547 or 5374835 or 6316793 or 6064082 or 5399886 or 20020066908 ).pn

## US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

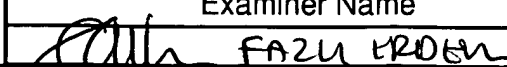
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
Fe	1	6639255	2003-10-28	Inoue, et al.			
P2	2	6483135	2002-11-19	Mizuta, et al.			
P3	3	6274889	2001-08-14	Ota, et al.			
P4	4	6184547	2001-02-06	Onda			
P5	5	5374835	1994-12-20	Shimada, et al.			
P6	6	6316793	2001-11-13	Sheppard, et al.			
P7	7	6064082	2000-05-16	Kawai, et al.			
P8	8	5399886	1995-03-21	Hasegawa			

## US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
P8	1	20020066908	2002-06-06	Smith			

## Signature

Examiner Name	Date
 FAZU PROSEN	03/10/05



## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.  
28569.7636SERIAL NO.  
10/711,134

Karou INOUE, et al.

FILING  
August 26, 2004GROUP  
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

R		Dang, et al., "Fabrication and characterisation of enhanced barrier AlGaIn/GaNHFET," Electronic Letters, 1st April 1999, Vol. 35, No. 7, pp. 602-603
R		Yu, et al., "Measurement of piezoelectrically induced charge in GaN/AlGaIn heterostructure field-effect transistors," Appl. Phys. Lett. 71 (19), 10 November 1997, pp. 2794-2796.

EXAMINER

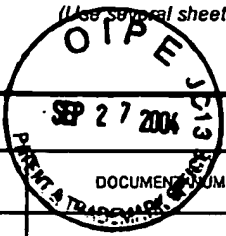
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						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

PB		•	Murphy, et al., "Normal and inverted AlGaIn/GaN based piezoelectric field effect transistors grown by plasma induced molecular beam epitaxy," MRS Internet J. Nitride Semicond. Res. 4S1, G8.4 (1999)
PB		•	Yu, et al., "Schottky barrier engineering in III-V nitrides via the piezoelectric effect," 28 September 1998, Applied Physics Letters, Vol. 73, No. 13, pp. 1880-1882

EXAMINER *Paul FAZLI BROTH*

DATE CONSIDERED 03/10/05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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